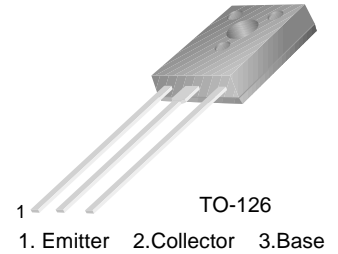


■ ■ APPLICATION: General Purpose Applications.

■ ■ MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	-40	V
Collector-emitter voltage	V_{CE0}	-25	V
Emitter-base voltage	V_{EBO}	-8	V
Collector current	I_C	-5	A
Power Dissipation	P_C	15	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$


■ ■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE1}	45		180		$V_{CE} = -1\text{V}, I_C = -2\text{A}$
	h_{FE2}	10				$V_{CE} = -2\text{V}, I_C = -5\text{A}$
Collector Cut-off Current	I_{CBO1}			-0.1	μA	$V_{CB} = -40\text{V}, I_E = 0$
	I_{CBO2}			-100	μA	$V_{CB} = -40\text{V}, I_E = 0, T_J = 125^\circ\text{C}$
Emitter Cut-off Current	I_{EBO}			-0.1	μA	$V_{EB} = -8\text{V}, I_C = 0$
Collector-Base Breakdown Voltage	BV_{CB0}	-40			V	$I_C = -1\text{mA}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CE0}	-25			V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-8			V	$I_E = -1\text{mA}, I_C = 0$
Base-Emitter Voltage	V_{BE}			-2.5	V	$V_{CE} = -1\text{V}, I_C = -2\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-1.8	V	$I_C = -5\text{A}, I_B = -1\text{A}$
	$V_{CE(sat)}$			-0.3	V	$I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-2.5	V	$I_C = -5\text{A}, I_B = -1\text{A}$
Gain bandwidth product	f_T	65			MHz	$I_C = -100\text{mA}, V_{CE} = -10\text{V}$
Feed Back Capacitance	C_{ob}			120	pF	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$

■ ■ hFE Classification

Classification

h_{FE1}	45~180
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